

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a first electrode;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole and connected with a third electrode through a second contact hole;
a second electrode provided on said insulating film; and
a liquid crystal layer provided over said second electrode,
wherein said first electrode overlaps with said second electrode with said insulating film interposed therebetween, and
wherein said second electrode is provided so as to block an electric field by said first electrode to said liquid crystal layer.
2. (Original) A semiconductor device according to claim 1, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.
3. (Original) A semiconductor device according to claim 1, wherein said second electrode is a pixel electrode.

4. (Original) A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

5. (Currently Amended) A semiconductor device comprising:
a semiconductor film;
a gate insulating film provided on said semiconductor film;
a first electrode which is provided on said gate insulating film and overlaps said semiconductor film;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole and connected with a third electrode through a second contact hole;
a second electrode provided on said insulating film; and
a liquid crystal layer provided over said second electrode,
wherein said first electrode overlaps with said second electrode with said insulating film interposed therebetween, and
wherein said second electrode is provided so as to block an electric field by said first electrode to said liquid crystal layer.

6. (Original) A semiconductor device according to claim 5, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

7. (Original) A semiconductor device according to claim 5, wherein said second electrode is a pixel electrode.

8. (Original) A semiconductor device according to claim 5, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

9. (Previously Presented) A semiconductor device comprising:

- a first semiconductor film;
- a second semiconductor film;
- a gate insulating film provided on said first semiconductor film and said second semiconductor film;
- a first electrode which is provided on said gate insulating film, intersects said first semiconductor film, and overlaps said second semiconductor film;
- an insulating film formed on said first electrode;
- a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
- a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole;
- a second electrode provided on said insulating film; and
- a liquid crystal layer provided over said second electrode,

wherein said first electrode overlaps with said second electrode with said insulating film interposed therebetween, and

wherein said second electrode is provided so as to block an electric field by said first electrode to said liquid crystal layer.

10. (Original) A semiconductor device according to claim 9, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

11. (Original) A semiconductor device according to claim 9, wherein said second electrode is a pixel electrode.

12. (Original) A semiconductor device according to claim 9, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

13. (Original) A semiconductor device comprising:
a first electrode;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and
a second electrode provided on said insulating film,
wherein said first electrode is overlapped at 70% or more of an area thereof with said second electrode.

14. (Original) A semiconductor device according to claim 13, further comprising a liquid crystal layer provided over said second electrode.

15. (Original) A semiconductor device according to claim 13, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

16. (Original) A semiconductor device according to claim 13, wherein said second electrode is a pixel electrode.

17. (Original) A semiconductor device according to claim 13, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

18. (Original) A semiconductor device comprising:
a semiconductor film;
a gate insulating film provided on said semiconductor film;
a first electrode which is provided on said gate insulating film and overlaps said semiconductor film;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and
a second electrode provided on said insulating film,
wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said semiconductor film and overlapped at 90% or more of an area thereof with said second electrode.

19. (Original) A semiconductor device according to claim 18, further comprising a liquid crystal layer provided over said second electrode.

20. (Original) A semiconductor device according to claim 18, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

21. (Original) A semiconductor device according to claim 18, wherein said second electrode is a pixel electrode.

22. (Original) A semiconductor device according to claim 18, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

23. (Original) A semiconductor device comprising:
a first semiconductor film;
a second semiconductor film;
a gate insulating film provided on said first semiconductor film and said second semiconductor film;
a first electrode which is provided on said gate insulating film, intersects said first semiconductor film, and overlaps said second semiconductor film;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and
a second electrode provided on said insulating film,
wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said second semiconductor film and overlapped at 90% or more of an area thereof with said second electrode.

24. (Original) A semiconductor device according to claim 23, further comprising a liquid crystal layer provided over said second electrode.

25. (Original) A semiconductor device according to claim 23, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

26. (Original) A semiconductor device according to claim 23, wherein said second electrode is a pixel electrode.

27. (Original) A semiconductor device according to claim 23, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.